# 2SK1339

#### Silicon N-Channel MOS FET

# **HITACHI**

ADE-208-1276 (Z) 1st. Edition Mar. 2001

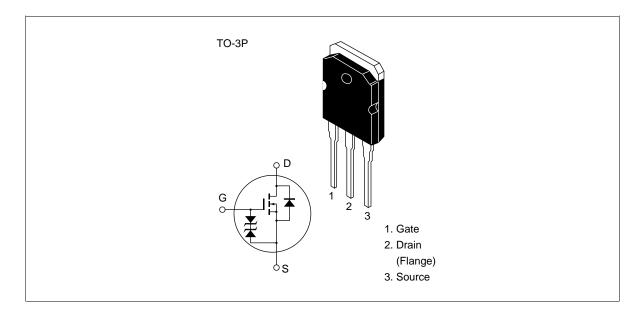
### **Application**

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

#### Outline





# 2SK1339

## **Absolute Maximum Ratings** $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{\scriptscriptstyle DSS}$	900	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	3	A
Drain peak current	I <sub>D(pulse)</sub> *1	7	А
Body to drain diode reverse drain current	I <sub>DR</sub>	3	Α
Channel dissipation	Pch*2	80	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10 µs, duty cycle 1%

2. Value at  $T_c = 25$ °C

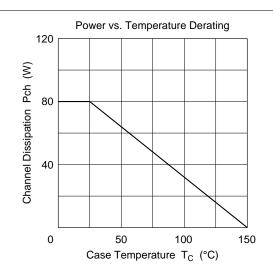
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

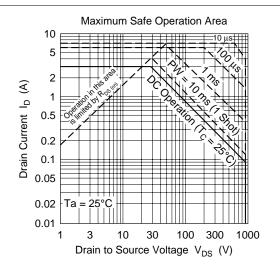
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	900	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$	
Gate to source leak current	$I_{\rm GSS}$	_	_	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$	
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	250	μΑ	$V_{DS} = 720 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	2.0	_	3.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	5.0	7.0		$I_D = 1.5 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$	
Forward transfer admittance	yfs	1.2	1.9	_	S	$I_D = 1.5 \text{ A}, V_{DS} = 20 \text{ V}^{*1}$	
Input capacitance	Ciss	_	425	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$	
Output capacitance	Coss	_	175	_	pF	f = 1 MHz	
Reverse transfer capacitance	Crss	_	85	_	pF		
Turn-on delay time	t <sub>d(on)</sub>	_	10	_	ns	$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V},$	
Rise time	t <sub>r</sub>	_	40	_	ns	R <sub>L</sub> = 15	
Turn-off delay time	$t_{d(off)}$	_	50	_	ns		
Fall time	t <sub>f</sub>	_	55	_	ns	<del></del>	
Body to drain diode forward voltage	$V_{DF}$		0.9		V	$I_F = 3 \text{ A}, V_{GS} = 0$	
Body to drain diode reverse recovery time	t <sub>rr</sub>	_	850	_	ns	$I_F = 3 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A/}\mu\text{s}$	

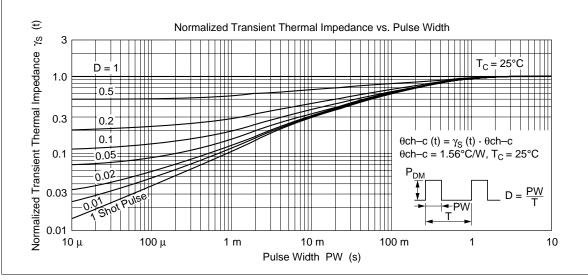
Note: 1. Pulse test

See characteristic curves of 2SK1338.

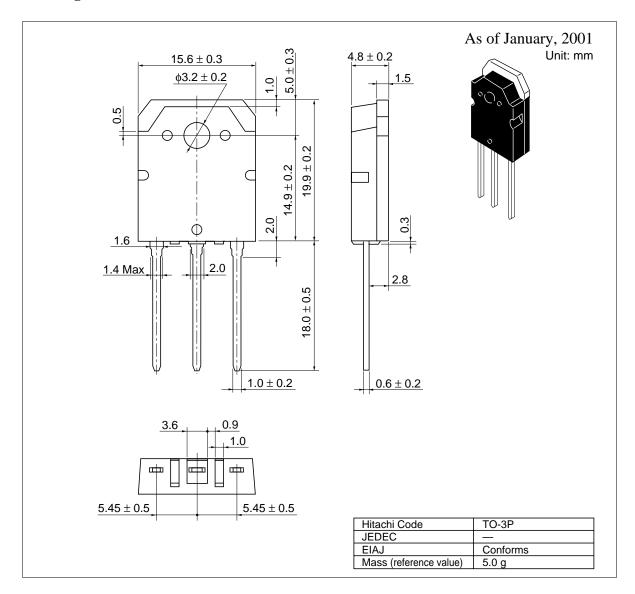
## 2SK1339







## **Package Dimensions**



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